



FIG. 1

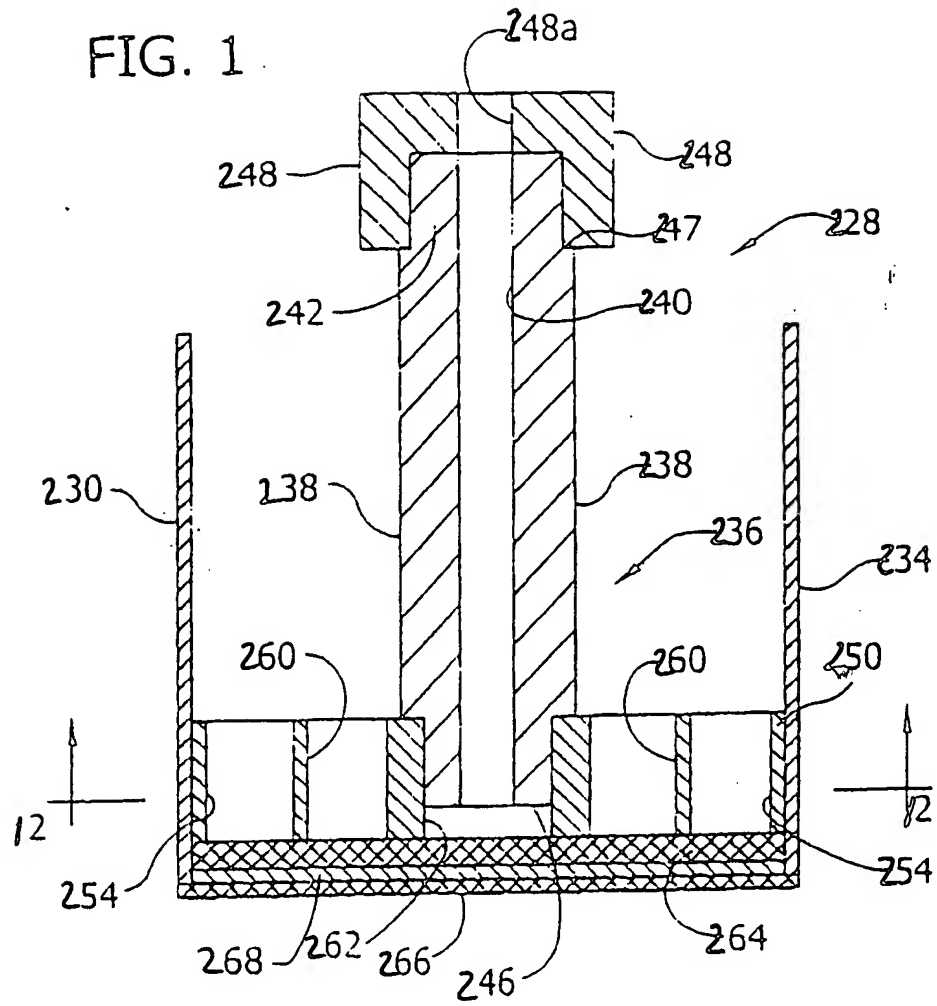


FIG. 2

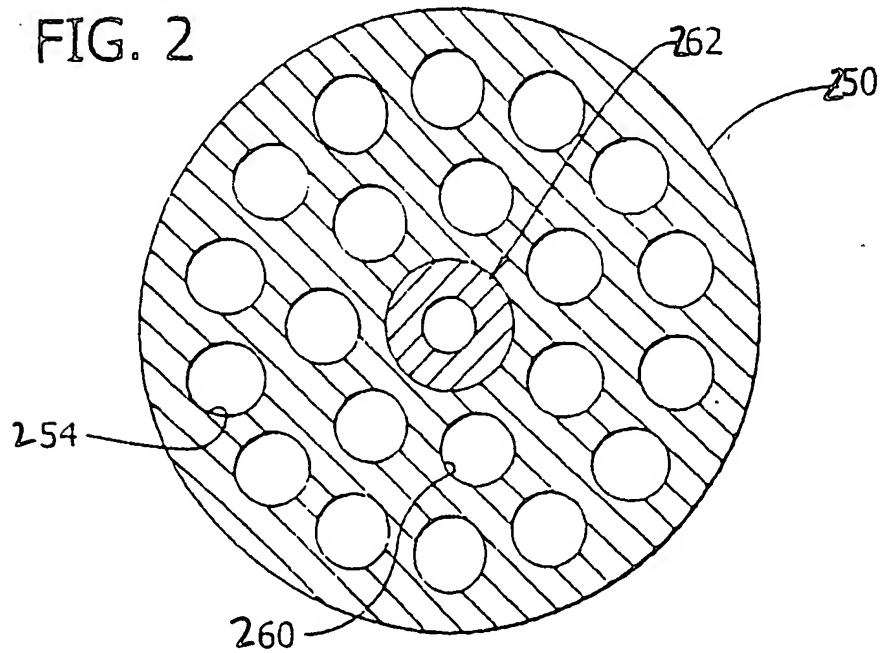


FIG. 1 is a cross-sectional view of a semiconductor device. The device includes a central vertical structure 240 with a top layer 248a and a base layer 248. This central structure is flanked by two vertical structures 230 and 234, which are part of a larger assembly 228. The base of the device is a substrate 254 with a cross-hatched pattern. The substrate is divided into regions 260, 262, 266, and 264. A central region 246 is also indicated. The device is shown in a cross-section along line 12-12.

FIG. 2

FIG. 2 is a cross-sectional view of a circular substrate 250. The substrate contains a grid of circular openings 260. A central opening 254 is filled with a hatched material 262.